

Linear Systems replaces discontinued Siliconix JPAD200

The LSJPAD200 is a low leakage Pico-Amp Diode packaged in TO-92

The LSJPAD200 extremely low-leakage diode provides a superior alternative to conventional diode technology when reverse current (leakage) must be minimized. The LSJPAD200 features a leakage current of -200 pA and is well suited for use in applications such as input protection for operational amplifiers.

LSJPAD200 Benefits:

- Negligible Circuit Leakage Contribution
- Circuit "Transparent" Except to Shunt High-Frequency Spikes
- Simplicity of Operation

LSJPAD200 Applications:

- Op Amp Input Protection
- Multiplexer Overvoltage Protection

FEATURES

DIRECT REPLACEMENT FOR SILICONIX JPAD200

REVERSE BREAKDOWN VOLTAGE	$BV_R \geq -35V$
ULTRALOW LEAKAGE	≤ 200 pA
REVERSE CAPACITANCE	$C_{RSS} \leq 2.0pF$

ABSOLUTE MAXIMUM RATINGS

@ 25°C (unless otherwise noted)

Maximum Temperatures

Storage Temperature	$-65^\circ C$ to $+150^\circ C$
Operating Junction Temperature	$-55^\circ C$ to $+135^\circ C$

Maximum Power Dissipation

Continuous Power Dissipation	350mW
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MAXIMUM CURRENT

Forward Current (Note 1)	10mA
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LSJPAD200 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
BV_R	Reverse Breakdown Voltage	-35	--	--	V	$I_R = -1\mu A$
V_F	Forward Voltage	--	0.8	1.5	V	$I_F = 5mA$
C_{RSS}	Total Reverse Capacitance	--	1.5	2	pF	$V_R = -5V, f = 1MHz$
I_R	Maximum Reverse Leakage Current	--	--	-200	pA	$V_R = -20V$

Notes:

1. Absolute maximum ratings are limiting values above which LSJPAD200 serviceability may be impaired.

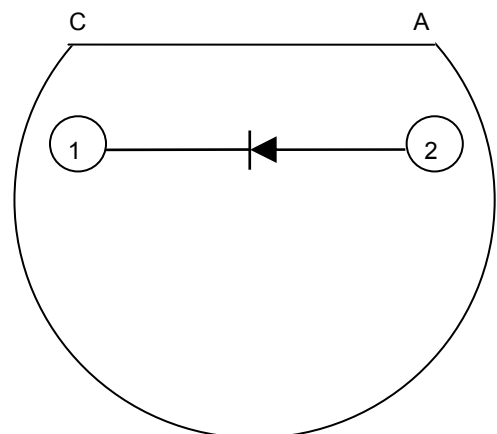
Available Packages:

LSJPAD200 in TO-92
LSJPAD200 available as bare die

Please contact Micross for full package and die dimensions



TO-92 (Bottom View)



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